



Form PTO-1449 (MAY 1997)				Atty Docket No.: 03692.P059DC		Serial No.: 10/722,792		
List of Patents and Publications Statement (Use several sheets if necessary)				Applicants: Disney, D.				
				Filing Date: November 25, 2003				
REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS				
Exam. Initial		Date	Document Number	Name	Class	Sub-Class	Filing Date	
FOREIGN PATENT DOCUMENTS								
No.		Document No.	Date	Country	Name	Class	Sub-Class	Trans-lation
		JP 56-38867	04/14/81	Japan	Okabe, T., et al.			English
		JP 57-10975	01/20/82	Japan	Sanyo			
		W/O 99/34449	07/08/99	PCT	Konin Klijke			
		JP 57-12557	01/22/82	Japan	Tanaka, T., et al.			
		JP 57-12558	01/22/82	Japan	Tanaka, T., et al.			
		JP 60-64471	04/13/85	Japan	Saiotou, M.			
		JP 3-211771	09/17/91	Japan	Toshiba			
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)								
		International Electron Device Meeting 1979 – Washington, D.C., Dec. 3-4-5, Sponsored by Electron Devices Society of IEEE, Pages 238-241						
		"Realization of High Breakdown Voltage (>700V) in Thin SOI Devices" S. Menchant, et al., Phillips Laboratories North American Phillips Corporation 1991 IEEE, Pages 31-35						
Examiner				Date Considered				
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

Form PTO-1449 (Modified)				Atty Docket No.: 03692.P059DC		Serial No.: 10/722,792	
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No.		Document No.	Date	Country	Name	Class	Sub-Class
		JP 4107877A	04/09/92	Japan	Yamanishi, et al.		
		JP 6-224426	08/12/94	Japan	Uno, et al.		English
		DE 43 09 764	09/29/94	Germany	Tihanyi, et al.		
		JP 04-107867	08/12/94	Japan	Kawasaki, et al.		
		JP 2000-349288	12/15/00	Japan	Ueno		English
		W/O 97 35346	11/25/97	PCT	Tihanyi		
		W/O 00 33385	06/08/00	PCT	Tihanyi		
		W/O 02 41402	05/23/02	PCT	Baliga, et al.		
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
		"Theory of Semiconductor Superjunction Devices," Fujihira, Japan Journal of Applied Physics Part 1, October 1997, Vol. 36, No.10, Pages 6254-6262					
		"Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance," B. Shieh, K.C. Sanaswat IEEE Electron Device Hettas, Vol. 19, No. 1, Jan. 1998					
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No.		Document No.	Date	Country	Name	Class	Sub-Class
		W/O 02 099909	12/12/02	PCT	Liang, et al.		
		EP 1073 123 A2	07/28/00	EP	Yasuhara		
		GB 2 309 336 A	01/21/97	UK	Fujihira		
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
		"Oxide-Bypassed VDMOS (OBVDMOS): An Alternative to Superjunction High-Voltage MOS Power Devices," Yung C. Liang, et al., August 2001, IEEE Electron Device Letters Vol. 22, No. 8, Pages 407-409					
		"Comparison of High-Voltage Devices for Power Integrated Circuits," R. Jay Anaman, et al., IEDM 84, Pages 258-261					
		"A New Generation of High-Voltage MOSFET's Breaks the Limit Line of Silicon," G. Debby, et al., Siemens AG, Semiconductor Division, Munchen, Germany; IEDM 98-683 to IEDM 98-685					
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
		"High Performance 600V Smart Power Technology Based on Thin Layer Silicon-on-Insulator," T. Levatic, et al., Philips Research, Philips Electronics North America Corporation, 4 Pages.					
		"Modern Semiconductor Device Physics," S.M. Sze, John Wiley & Sons, Chapter 4 ("Power Devices") pp.203-206, (1998)					
		"Modeling Optimization of Lateral High-Voltage IC Devices to Minimize 3-D Effects," Hamza Yilmaz, R&D Engineering, Semiconductor Business Division, General Electric Company, NC, pp. 290-297					
		"Optimization of the Specific On-Resistance of the COOLMOS™," Chen, et al., IEEE Transactions on Electronic Devices, Vol. 48, no. 2, February 2001					
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
		"Lateral Unbalanced Super Junction (USJ) / 3D-RESURF for High Breakdown Voltage on SOI," Ng, et al., pp. 395-398, 04/06/2001					
		"Static and Dynamic Electricity," William R. Smythe, McGraw-Hill Book Company, Inc., New York, 1950.					
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	Method of Fabricating a High-Voltage Transistor With A Multi-Layered Extended Drain Structure						
Application Number:	10/722792						
Confirmation Number:	7244						
First Named Applicant:	Donald Disney						
Attorney Docket Number:	03692.P059DC						
Art Unit:	2818						
Examiner:	David Nhu						
Search string:	(6184555 or 6462377 or 6127703 or 5306656 or 6525372 or 6468847 or 5973360 or 5637898 or 5665994 or 4929987 or 4531173 or 6573558 or 6555873 or 6509220 or 6667213 or 6635544 or 6365932 or 4626789 or 6294818 or 5760440 or 6049108 or 5821144 or 4738936 or 5869875 or 6191447 or 4343015 or 6388286 or 6194283 or 4890144 or 6353252 or 6207994 or 5155574 or 5146298 or 4811075 or 4626879 or 4890146 or 5237193 or 5368136 or 5313082 or 5068700 or 5258636 or 20020175351 or 20020056884 or 20010015459),pn.						
US Patent Documents							
Note: Applicant is not required to submit a paper copy of cited US Patent Documents							
Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6184555	2001-02-06	Tihanyi et al.	B1		
	2	6462377	2002-10-08	Hurky et al.	B2		
	3	6127703	2000-10-03	Letavic et al.			
	4	5306656	1994-04-26	Williams et al.			
	5	6525372	2003-02-25	Baliga	B2		
	6	6468847	2002-10-22	Disney	B1		
	7	5973360	1999-10-26	Tihanyi			
	8	5637898	1997-06-10	Baliga			
	9	5665994	1997-09-09	Palara			

10	4929987	1990-05-01	Einthoven	
11	4531173	1985-07-23	Yamada	
12	6573558	2003-06-03	Disney	B2
13	6555873	2003-04-29	Disney et al.	B2
14	6509220	2003-01-21	Disney	B2
15	6667213	2003-12-23	Disney	B2
16	6635544	2003-10-21	Disney	B2
17	6365932	2002-04-02	Kouno et al.	
18	4626789	1986-12-01	Nakata et al.	
19	6294818	2001-09-25	Fujihira	B1
20	5760440	1998-06-02	Kitamura et al.	
21	6049108	2000-04-11	Williams et al.	
22	5821144	1998-10-13	D'Anna et al.	
23	4738936	1988-04-19	Rice	
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27	6388286	2002-05-01	Baliga	B1
28	6194283	2001-02-01	Gardner et al.	
29	4890144	1989-12-01	Teng et al.	
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31	6207994	2001-03-27	Rumennik et al.	
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33	5146298	1992-09-08	Eklund	
34	4811075	1989-03-07	Eklund	
35	4626879	1986-12-02	Colak	
36	4890146	1989-12-26	Williams	
37	5237193	1993-08-17	Williams et al.	
38	5368136	1995-01-03	Williams et al.	
39	5313082	1994-05-17	Eklund	
40	5068700	1991-11-26	Yamaguchi et al.	
41	5258636	1993-11-02	Rumennik et al.	

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

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init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20020175351	2002-11-28	Baliga	A1		
	2	20020056884	2002-05-16	Baliga	A1		
	3	20010015459	2001-08-23	Watanabe et al.	A1		

Signature

Examiner Name	Date